

# ABSTRACT

A strained Si layer 2 is epitaxially grown on a base SiGe layer 1, and a gate insulating film 3a and a gate electrode 4a are formed. An impurity is then ion-implanted (FIG. 2A) into  
5 the base SiGe layer 1 and the strained Si layer 2 using the gate electrode 4a as a mask, heat treatment is performed for activation, and a source/drain region 6 is formed (FIGS. 2B and 2C). In this instance, the film thickness of the strained Si layer 2 is set to  $2T_p$ , where  $T_p$  ( $= R_p$ ) is the depth having  
10 the maximum concentration of the impurity in the source/drain region 6 of the finished MISFET.